Understanding RowHammer Under Reduced Wordline Voltage

An Experimental Study Using Real DRAM Devices

Session 14 (June 30, 10:30 AM) Hardware and Software Security

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Executive Summary

Motivation:

- Repeatedly **toggling a DRAM row's wordline voltage** causes bit flips in nearby rows
- This vulnerability, RowHammer, worsens in denser DRAM chips
- Understanding RowHammer enables designing effective and efficient solutions

Problem: No study demonstrates how wordline voltage (V_{PP}) affects RowHammer

Goal: Experimentally understand how V_{PP} affects RowHammer and DRAM operation

Experimental study: 272 DRAM chips from **three major manufacturers**

VPP's effect on RowHammer: *Six observations* show that with reduced V_{PP},

- A row needs to be hammered **7.4% more times (85.8% max)** to induce a bit flip
- Bit error rate caused by a RowHammer attack reduces by 15.2% (66.9% max)

VPP's effect on DRAM operation: *Nine observations* show that with reduced V_{PP},

- 208 out of 272 tested DRAM chips reliably operate using nominal timing parameters
- Erroneous DRAM chips can reliably operate with
 - A longer row activation latency, i.e., 24ns/15ns for 48/16 chips,
 - Single-error-correcting codes or 2x the refresh rate only for 16.4% of rows

<u>Conclusion</u>: Scaling down the wordline voltage can <u>reduce RowHammer vulnerability</u> without significantly affecting reliable DRAM operation

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